

REVISIONS

LTR	DESCRIPTION	DATE (YR-MO-DA)	APPROVED
A	Add device types 02 and 03. Make change to the NPN and PNP characteristics hFE tests as specified under Table I. Delete NPN and PNP characteristics ICEO and ICBO tests as specified under Table I. - ro	08-04-08	R. Heber
B	Add case outline X. Make changes to 1.2.4, 1.3, and Figure 1. - ro	09-03-17	R. Heber
C	Add device types 04, 05, and 06. Delete figure 2. Remove radiation exposure circuits, paragraph 4.4.4.2 Dose rate burnout, and references to device class M requirements. - ro	14-09-11	C. Saffle
D	Update paragraphs to MIL-PRF-38535 requirements. - drw	20-04-17	James R. Eschmeyer



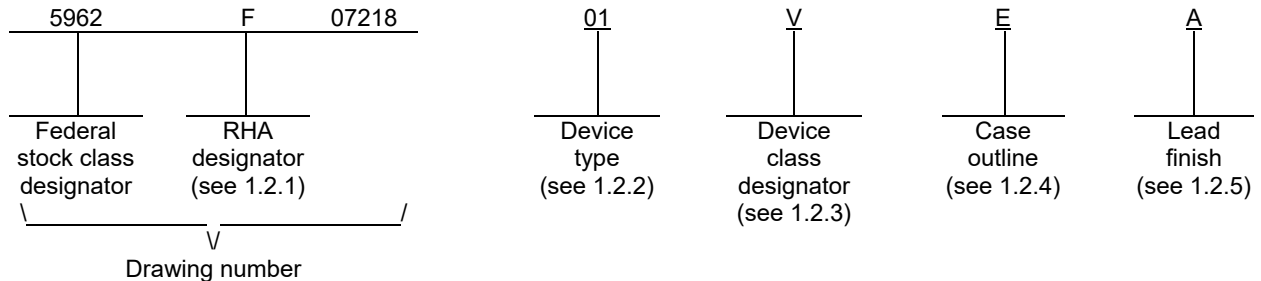
REV																				
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REV STATUS				REV	D	D	D	D	D	D	D	D	D	D	D	D	D	D	D	
OF SHEETS				SHEET	1	2	3	4	5	6	7	8	9	10	11	12	13	14		

PMIC N/A	PREPARED BY Rick Officer		<p align="center">DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990 https://www.dla.mil/LandandMaritime</p>																
<p align="center">STANDARD MICROCIRCUIT DRAWING</p> <p>THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE</p>	CHECKED BY Rajesh Pithadia																		
	APPROVED BY Robert M. Heber																		
	DRAWING APPROVAL DATE 07-04-17																		
	REVISION LEVEL D																		
AMSC N/A	SIZE A	CAGE CODE 67268	5962-07218																
			SHEET 1 OF 18																

1. SCOPE

1.1 Scope. This drawing documents two product assurance class levels consisting of high reliability (device class Q) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels is reflected in the PIN.

1.2 PIN. The PIN is as shown in the following example:



1.2.1 RHA designator. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 Device types. The device types identify the circuit function as follows:

<u>Device type</u>	<u>Generic number</u>	<u>Circuit function</u>
01	ISL73096RH	Radiation hardened, dielectrically isolated, ultra high frequency all NPN – PNP combination transistor array
02	ISL73127RH	Radiation hardened, dielectrically isolated, ultra high frequency all NPN transistor array
03	ISL73128RH	Radiation hardened, dielectrically isolated, ultra high frequency all PNP transistor array
04	ISL73096EH	Radiation hardened, dielectrically isolated, ultra high frequency all NPN – PNP combination transistor array
05	ISL73127EH	Radiation hardened, dielectrically isolated, ultra high frequency all NPN transistor array
06	ISL73128EH	Radiation hardened, dielectrically isolated, ultra high frequency all PNP transistor array

1.2.3 Device class designator. The device class designator is a single letter identifying the product assurance level as follows:

<u>Device class</u>	<u>Device requirements documentation</u>
Q or V	Certification and qualification to MIL-PRF-38535

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1.2.4 Case outlines. The case outlines are as designated in MIL-STD-1835 as follows:

<u>Outline letter</u>	<u>Descriptive designator</u>	<u>Terminals</u>	<u>Package style</u>
E	CDIP2-T16	16	Dual-in-line
X	CDFP4-16	16	Flat pack

1.2.5 Lead finish. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V.

1.3 Absolute maximum ratings. 1/

Collector to emitter voltage (open base) :	
Device types 01, 02, 04, 05 (NPN characteristics)	+8 V
Device types 01, 03, 04, 06 (PNP characteristics)	-8 V
Collector to base voltage (open emitter) :	
Device types 01, 02, 04, 05 (NPN characteristics)	+12 V
Device types 01, 03, 04, 06 (PNP characteristics)	-10 V
Emitter to base voltage (reverse bias) :	
Device types 01, 02, 04, 05 (NPN characteristics)	+5.5 V
Device types 01, 03, 04, 06 (PNP characteristics)	-4.5 V
Collector current at 100% duty cycle, +175°C	11.3 mA
Maximum power dissipation (PD) :	
Case outline E	555 mW
Case outline X :	
At +25°C	1.25 W
At +125°C	0.41 W
Junction temperature (T _J)	+175°C
Storage temperature range	-65°C ≤ T _A ≤ +150°C
Lead temperature (soldering, 10 seconds)	+265°C
Thermal resistance, junction-to-case (θ _{JC}) :	
Case outline E	See MIL-STD-1835
Case outline X	28°C/W
Thermal resistance, junction-to-ambient (θ _{JA}) :	
Case outline E	90°C/W
Case outline X	120°C/W

1.4 Recommended operating conditions.

Ambient operating temperature range (T _A)	-55°C ≤ T _A ≤ +125°C
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1.5 Radiation features.

Maximum total dose available (dose rate = 50 – 300 rads(Si)/s):	
Device types 01, 02, and 03	300 krads(Si) 2/
Device type 04, 05, and 06	300 krads(Si) 3/
Maximum total dose available (dose rate ≤ 0.01 rad(Si)/s):	
Device types 04, 05, and 06	50 krads(Si) 3/

- 1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.
- 2/ Device types 01, 02 and 03 may be dose rate sensitive in a space environment and may demonstrate enhanced low dose rate effects. Device types 01, 02, and 03 radiation end point limits for the noted parameters are guaranteed only for the conditions as specified in MIL-STD-883, method 1019, condition A to a maximum total dose of 300 krads(Si).
- 3/ Device types 04, 05, and 06 radiation end point limits for the noted parameters are guaranteed only for the conditions as specified in MIL-STD-883, method 1019, condition A to a maximum total dose of 300 krads(Si), and condition D to a maximum total dose of 50 krads(Si).

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2. APPLICABLE DOCUMENTS

2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard Microcircuits.
MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings.
MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at <https://quicksearch.dla.mil>.)

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 Item requirements. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 as specified herein, or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

3.1.1 Microcircuit die. For the requirements of microcircuit die, see appendix A to this document.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V.

3.2.1 Case outlines. The case outlines shall be in accordance with 1.2.4 herein.

3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.

3.2.5 Radiation exposure circuit. The radiation exposure circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing and acquiring activity upon request.

3.3 Electrical performance characteristics and postirradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.

3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table I.

3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535.

3.5.1 Certification/compliance mark. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535.

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TABLE I. Electrical performance characteristics.

Test	Symbol	Conditions -55°C ≤ TA ≤ +125°C unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
NPN characteristics							
Collector to base breakdown voltage	V(BR)CBO	IC = 100 μA, IE = 0 M,D,P,L,R,F 1/, 2/	1, 2, 3	01, 02,	12		V
			1	04, 05	12		
Collector to emitter breakdown voltage	V(BR)CEO	IC = 100 μA, IB = 0 M,D,P,L,R,F 1/, 2/	1, 2, 3	01, 02,	8		V
			1	04, 05	8		
Collector to emitter breakdown voltage	V(BR)CES	IC = 100 μA, base shorted to emitter M,D,P,L,R,F 1/, 2/	1, 2, 3	01, 02, 04, 05	10		V
			1		10		
Emitter to base breakdown voltage	V(BR)EBO	IE = 10 μA, IC = 0 M,D,P,L,R,F 1/, 2/	1, 2, 3	01, 02,	5.5		V
			1	04, 05	5.5		
Collector to emitter saturation voltage	VCE(SAT)	IC = 10 mA, IB = 1 mA M,D,P,L,R,F 1/, 2/	1, 2, 3	01, 02,		0.5	V
			1	04, 05		0.5	
Base to emitter voltage	VBE	IC = 10 mA M,D,P,L,R,F 1/, 2/	1	01, 02,		0.95	V
			2, 3	04, 05		1.05	
			1			1.05	
DC forward current transfer ratio	hFE	IC = 10 mA, VCE = 2 V M,D,P,L,R,F 1/, 2/	1	01, 02,	80		
			2, 3	04, 05	40		
			1		40		
Early voltage	VA	IC = 1 mA, VCE = 3.5 V M,D,P,L,R,F 1/, 2/	1, 2, 3	01, 02,	20		V
			1	04, 05	20		

See footnotes at end of table.

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TABLE I. Electrical performance characteristics – continued.

Test	Symbol	Conditions -55°C ≤ TA ≤ +125°C unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
PNP characteristics							
Collector to base breakdown voltage	V(BR)CBO	IC = -100 μA, IE = 0 M,D,P,L,R,F <u>1/</u> , <u>2/</u>	1, 2, 3	01, 03,	10		V
			1	04, 06	10		
Collector to emitter breakdown voltage	V(BR)CEO	IC = -100 μA, IB = 0 M,D,P,L,R,F <u>1/</u> , <u>2/</u>	1, 2, 3	01, 03,	8		V
			1	04, 06	8		
Collector to emitter breakdown voltage	V(BR)CES	IC = -100 μA, base shorted to emitter M,D,P,L,R,F <u>1/</u> , <u>2/</u>	1, 2, 3	01, 03, 04, 06	10		V
			1		10		
Emitter to base breakdown voltage	V(BR)EBO	IE = -10 μA, IC = 0 M,D,P,L,R,F <u>1/</u> , <u>2/</u>	1, 2, 3	01, 03,	4.5		V
			1	04, 06	4.5		
Collector to emitter saturation voltage	VCE(SAT)	IC = -10 mA, IB = -1 mA M,D,P,L,R,F <u>1/</u> , <u>2/</u>	1, 2, 3	01, 03,		0.5	V
			1	04, 06		0.5	
Base to emitter voltage	VBE	IC = -10 mA M,D,P,L,R,F <u>1/</u> , <u>2/</u>	1	01, 03,		0.95	V
			2, 3	04, 06		1.05	
			1			1.05	
DC forward current transfer ratio	hFE	IC = -10 mA, VCE = -2 V M,D,P,L,R,F <u>1/</u> , <u>2/</u>	1	01, 03,	40		
			2, 3	04, 06	20		
			1		20		
Early voltage	VA	IC = -1 mA, VCE = -3.5 V M,D,P,L,R,F <u>1/</u> , <u>2/</u>	1, 2, 3	01, 03,	10		V
			1	04, 06	10		

1/ RHA device types 01, 02, and 03 supplied to this drawing will meet all levels M, D, P, L, R and F of irradiation. However, device types 01, 02, and 03 are only tested at the “F” level in accordance with MIL-STD-883 method 1019 condition A (see 1.5 herein).

RHA device types 04, 05, and 06 supplied to this drawing will meet all levels M, D, P, L, R, and F of irradiation for condition A and levels M, D, P, and L for condition D. However, device types 04, 05, and 06 are only tested at the “F” level in accordance with MIL-STD-883, method 1019, condition A, and tested at the “L” level in condition D (see 1.5 herein).

Pre and post irradiation values are identical unless otherwise specified in table I. When performing post irradiation electrical measurements for any RHA level, TA = +25°C.

2/ Device types 01, 02 and 03 may be dose rate sensitive in a space environment and may demonstrate enhanced low dose rate effects.

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Device types	01 and 04	02, 03, 05, and 06
Case outlines	E and X	
Terminal number	Terminal symbol	
1	Q1 base	Q1 collector
2	Q1 emitter	Q2 collector
3	Q1 collector	Q2 emitter
4	Q2 emitter	Q2 base
5	Q2 base	NC
6	Q2 collector	Q3 collector
7	Q3 emitter	Q3 emitter
8	Q3 base	Q3 base
9	Q3 collector	Q4 base
10	Q4 emitter	Q4 emitter
11	Q4 base	Q4 collector
12	Q4 collector	Q5 collector
13	Q5 emitter	Q5 emitter
14	Q5 base	Q5 base
15	Q5 collector	Q1 base
16	NC	Q1 emitter

NC = No connection

FIGURE 1. Terminal connections.

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3.6 Certificate of compliance. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). The certificate of compliance submitted to DLA Land and Maritime-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein.

3.7 Certificate of conformance. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 shall be provided with each lot of microcircuits delivered to this drawing.

4. VERIFICATION

4.1 Sampling and inspection. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection.

4.2.1 Additional criteria for device classes Q and V.

- a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.
- b. Interim and final electrical test parameters shall be as specified in table IIA herein.
- c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.

4.3 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4 Conformance inspection. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections, and as specified herein.

4.4.1 Group A inspection.

- a. Tests shall be as specified in table IIA herein.
- b. Subgroups 4, 5, 6, 7, 8, 9, 10, and 11 in table I, method 5005 of MIL-STD-883 shall be omitted.

4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table IIA herein.

4.4.2.1 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.

4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table IIA herein.

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TABLE IIA. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-PRF-38535, table III)	
	Device class Q	Device class V
Interim electrical parameters (see 4.2)	1	1
Final electrical parameters (see 4.2)	1, 2, 3 <u>1/</u>	1, 2, 3 <u>1/</u> , <u>2/</u>
Group A test requirements (see 4.4)	1, 2, 3	1, 2, 3
Group C end-point electrical parameters (see 4.4)	1	1 <u>2/</u>
Group D end-point electrical parameters (see 4.4)	1	1
Group E end-point electrical parameters (see 4.4)	1	1

1/ PDA applies to subgroup 1.

2/ Delta limits as specified in table IIB shall be required where specified, and the delta limits shall be completed with reference to the zero hour electrical parameters (see table I).

TABLE IIB. Burn-in and operating life test delta parameters. $T_A = +25^{\circ}\text{C}$.

Parameters	Symbol	Device types	Delta limit
Collector to emitter saturation voltage	VCE(SAT)	04, 05, 06	± 75 mV
Base to emitter voltage	VBE		± 150 mV

1/ Deltas are performed at room temperature.

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4.4.4 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).

- a. End-point electrical parameters shall be as specified in table IIA herein.
- b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at $T_A = +25^{\circ}\text{C} \pm 5^{\circ}\text{C}$, after exposure, to the subgroups specified in table IIA herein.

4.4.4.1 Total dose irradiation testing. Total dose irradiation testing shall be performed in accordance with MIL-STD-883 method 1019, condition A and as specified herein for device types 01, 02, 03, 04, 05, and 06. In addition, for device types 04, 05, and 06 a low dose rate test shall be performed in accordance with MIL-STD-883 method 1019, condition D and as specified herein.

4.4.4.1.1 Accelerated annealing test. Accelerated annealing tests shall be performed on all devices requiring a RHA level greater than 5 krad(SI). The post-anneal end-point electrical parameter limits shall be as specified in table I herein and shall be the pre-irradiation end-point electrical parameter limit at $25^{\circ}\text{C} \pm 5^{\circ}\text{C}$. Testing shall be performed at initial qualification and after any design or process changes which may affect the RHA response of the device.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V.

6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor prepared specification or drawing.

6.2 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.

6.3 Record of users. Military and industrial users should inform DLA Land and Maritime when a system application requires configuration control and which SMD's are applicable to that system. DLA Land and Maritime will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DLA Land and Maritime-VA, telephone (614) 692-8108.

6.4 Comments. Comments on this drawing should be directed to DLA Land and Maritime-VA, Columbus, Ohio 43218-3990, or telephone (614) 692-0540.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

6.6 Sources of supply.

6.6.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in MIL-HDBK-103 and QML-38535. The vendors listed in MIL-HDBK-103 and QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DLA Land and Maritime-VA and have agreed to this drawing.

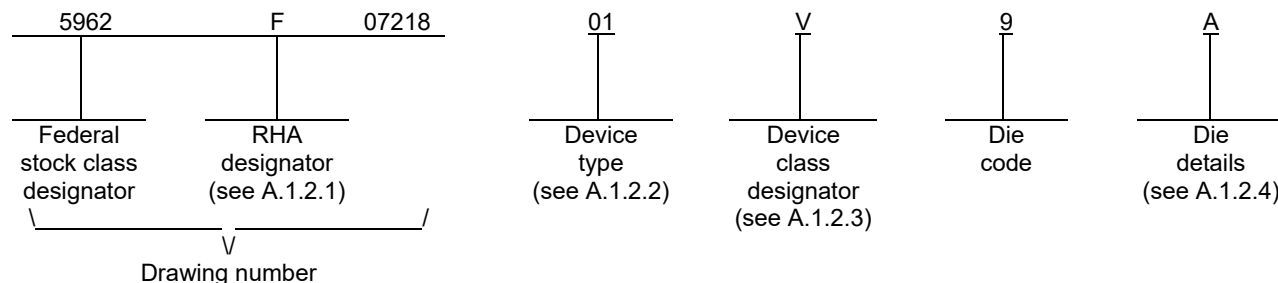
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APPENDIX A
APPENDIX A FORMS A PART OF SMD 5962-07218

A.1 SCOPE

A.1.1 Scope. This appendix establishes minimum requirements for microcircuit die to be supplied under the Qualified Manufacturers List (QML) Program. QML microcircuit die meeting the requirements of MIL-PRF-38535 and the manufacturers approved QM plan for use in monolithic microcircuits, multi-chip modules (MCMs), hybrids, electronic modules, or devices using chip and wire designs in accordance with MIL-PRF-38534 are specified herein. Two product assurance classes consisting of military high reliability (device class Q) and space application (device class V) are reflected in the Part or Identification Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.

A.1.2 PIN. The PIN is as shown in the following example:



A.1.2.1 RHA designator. Device classes Q and V RHA identified die meet the MIL-PRF-38535 specified RHA levels. A dash (-) indicates a non-RHA die.

A.1.2.2 Device types. The device types identify the circuit function as follows:

<u>Device type</u>	<u>Generic number</u>	<u>Circuit function</u>
01	ISL73096RH	Radiation hardened dielectrically isolated ultra high frequency all NPN-PNP combination transistor array
02	ISL73127RH	Radiation hardened, dielectrically isolated, ultra high frequency all NPN transistor array
03	ISL73128RH	Radiation hardened, dielectrically isolated, ultra high frequency all PNP transistor array
04	ISL73096EH	Radiation hardened, dielectrically isolated, ultra high frequency all NPN – PNP combination transistor array
05	ISL73127EH	Radiation hardened, dielectrically isolated, ultra high frequency all NPN transistor array
06	ISL73128EH	Radiation hardened, dielectrically isolated, ultra high frequency all PNP transistor array

A.1.2.3 Device class designator.

<u>Device class</u>	<u>Device requirements documentation</u>
Q or V	Certification and qualification to the die requirements of MIL-PRF-38535

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APPENDIX A
APPENDIX A FORMS A PART OF SMD 5962-07218

A.1.2.4 Die details. The die details designation is a unique letter which designates the die's physical dimensions, bonding pad location(s) and related electrical function(s), interface materials, and other assembly related information, for each product and variant supplied to this appendix.

A.1.2.4.1 Die physical dimensions.

<u>Die type</u>	<u>Figure number</u>
01, 02, 03, 04, 05, 06	A-1

A.1.2.4.2 Die bonding pad locations and electrical functions.

<u>Die type</u>	<u>Figure number</u>
01, 02, 03, 04, 05, 06	A-1

A.1.2.4.3 Interface materials.

<u>Die type</u>	<u>Figure number</u>
01, 02, 03, 04, 05, 06	A-1

A.1.2.4.4 Assembly related information.

<u>Die type</u>	<u>Figure number</u>
01, 02, 03, 04, 05, 06	A-1

A.1.3 Absolute maximum ratings. See paragraph 1.3 herein for details.

A.1.4 Recommended operating conditions. See paragraph 1.4 herein for details.

A.2 APPLICABLE DOCUMENTS.

A.2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARD

MIL-STD-883 - Test Method Standard Microcircuits.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings.

MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at <https://quicksearch.dla.mil>.)

A.2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

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APPENDIX A
APPENDIX A FORMS A PART OF SMD 5962-07218

A.3 REQUIREMENTS

A.3.1 Item requirements. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

A.3.2 Design, construction and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein and the manufacturer's QM plan for device classes Q and V.

A.3.2.1 Die physical dimensions. The die physical dimensions shall be as specified in A.1.2.4.1 and on figure A-1.

A.3.2.2 Die bonding pad locations and electrical functions. The die bonding pad locations and electrical functions shall be as specified in A.1.2.4.2 and on figure A-1.

A.3.2.3 Interface materials. The interface materials for the die shall be as specified in A.1.2.4.3 and on figure A-1.

A.3.2.4 Assembly related information. The assembly related information shall be as specified in A.1.2.4.4 and on figure A-1.

A.3.2.5 Radiation exposure circuit. The radiation exposure circuit shall be as defined in paragraph 3.2.3 herein.

A.3.3 Electrical performance characteristics and post-irradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and post-irradiation parameter limits are as specified in table I of the body of this document.

A.3.4 Electrical test requirements. The wafer probe test requirements shall include functional and parametric testing sufficient to make the packaged die capable of meeting the electrical performance requirements in table I.

A.3.5 Marking. As a minimum, each unique lot of die, loaded in single or multiple stack of carriers, for shipment to a customer, shall be identified with the wafer lot number, the certification mark, the manufacturer's identification and the PIN listed in A.1.2 herein. The certification mark shall be a "QML" or "Q" as required by MIL-PRF-38535.

A.3.6 Certification of compliance. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see A.6.4 herein). The certificate of compliance submitted to DLA Land and Maritime -VA prior to listing as an approved source of supply for this appendix shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and the requirements herein.

A.3.7 Certificate of conformance. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 shall be provided with each lot of microcircuit die delivered to this drawing.

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A.4 VERIFICATION

A.4.1 Sampling and inspection. For device classes Q and V, die sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modifications in the QM plan shall not affect the form, fit, or function as described herein.

A.4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and as defined in the manufacturer's QM plan. As a minimum, it shall consist of:

- a. Wafer lot acceptance for class V product using the criteria defined in MIL-STD-883, method 5007.
- b. 100% wafer probe (see paragraph A.3.4 herein).
- c. 100% internal visual inspection to the applicable class Q or V criteria defined in MIL-STD-883, method 2010 or the alternate procedures allowed in MIL-STD-883, method 5004.

A.4.3 Conformance inspection.

A.4.3.1 Group E inspection. Group E inspection is required only for parts intended to be identified as radiation assured (see A.3.5 herein). RHA levels for device classes Q and V shall be as specified in MIL-PRF-38535. End point electrical testing of packaged die shall be as specified in table IIA herein. Group E tests and conditions are as specified in paragraphs 4.4.4, 4.4.4.1, 4.4.4.1.1 herein.

A.5 DIE CARRIER

A.5.1 Die carrier requirements. The requirements for the die carrier shall be accordance with the manufacturer's QM plan or as specified in the purchase order by the acquiring activity. The die carrier shall provide adequate physical, mechanical and electrostatic protection.

A.6 NOTES

A.6.1 Intended use. Microcircuit die conforming to this drawing are intended for use in microcircuits built in accordance with MIL-PRF-38535 or MIL-PRF-38534 for government microcircuit applications (original equipment), design applications, and logistics purposes.

A.6.2 Comments. Comments on this appendix should be directed to DLA Land and Maritime -VA, Columbus, Ohio, 43218-3990 or telephone (614)-692-0540.

A.6.3 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

A.6.4 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in MIL-HDBK-103 and QML-38535. The vendors listed within MIL-HDBK-103 and QML-38535 have submitted a certificate of compliance (see A.3.6 herein) to DLA Land and Maritime -VA and have agreed to this drawing.

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Device types 01 and 04

(2) Q1E (1) Q1B (16) NC (15) Q5C

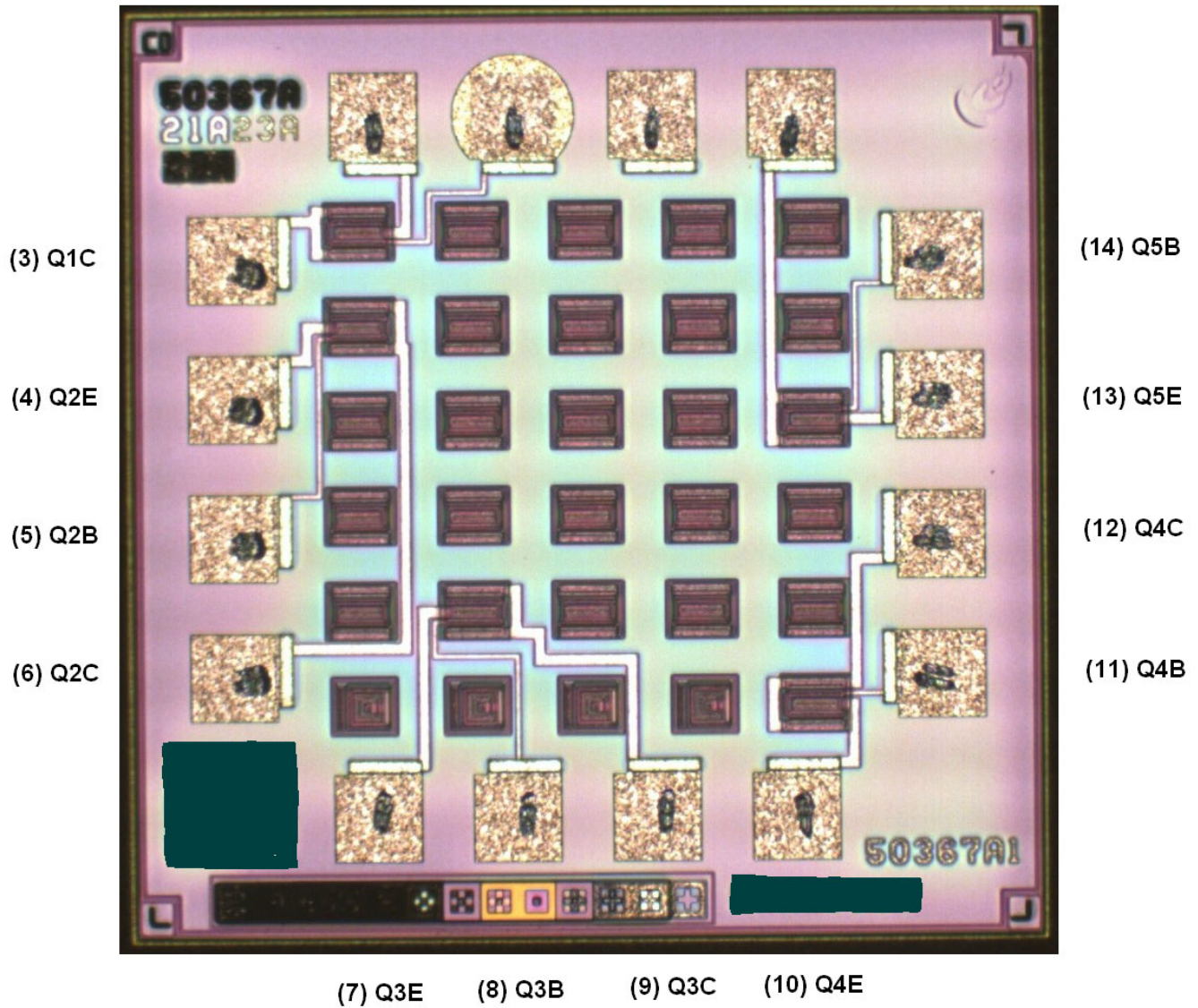


FIGURE A-1. Die bonding pad locations and electrical functions.

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Device types 02 and 05

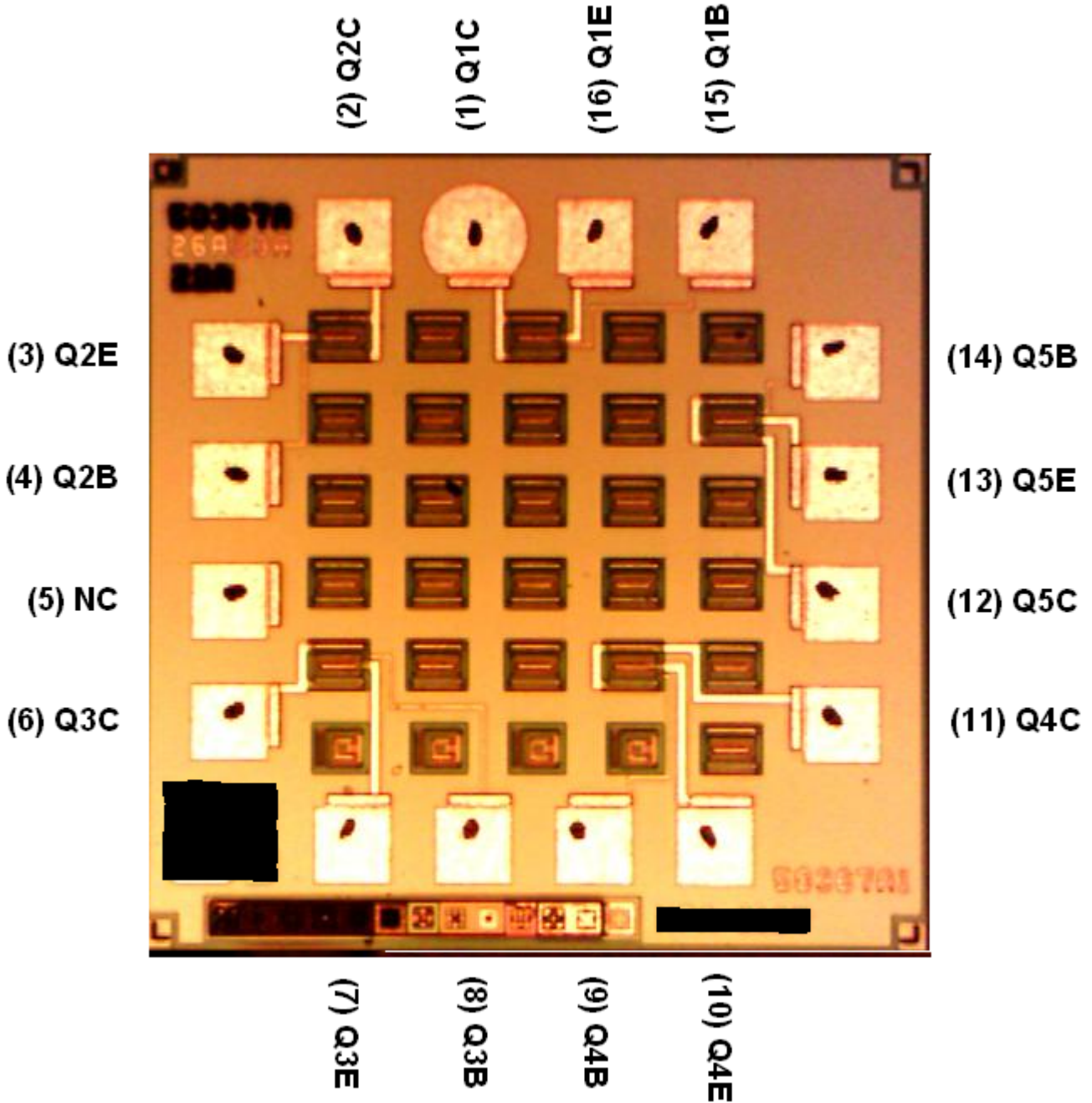


FIGURE A-1. Die bonding pad locations and electrical functions – continued.

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Device types 03 and 06

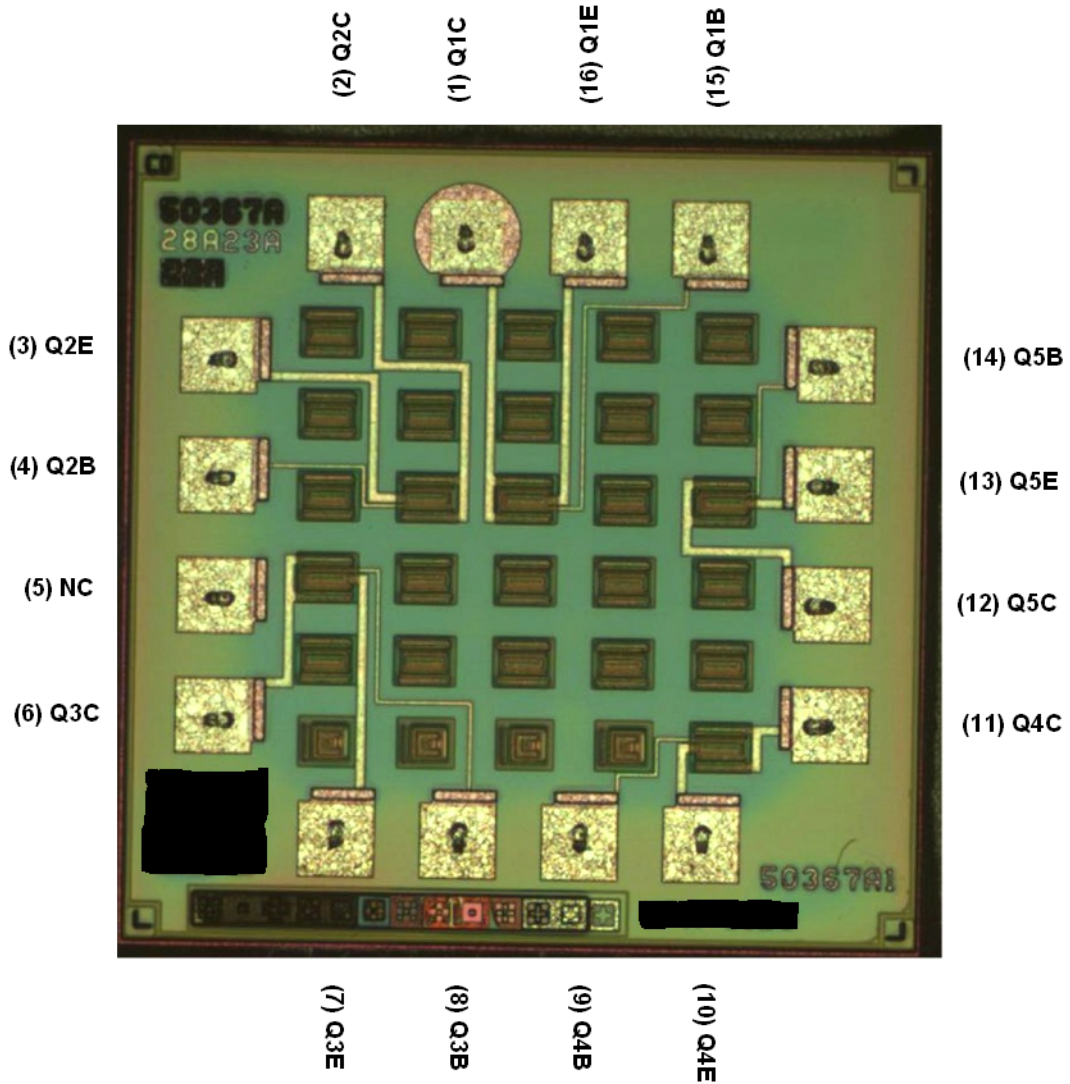


FIGURE A-1. Die bonding pad locations and electrical functions - continued.

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Die bonding pad locations and electrical functions

Die physical dimensions.

Die size: 1340 microns x 1320 microns

Die thickness: 14 ± 1 mils

Interface materials.

Top metallization: AlCu $16.0 \text{ k}\text{\AA} \pm 0.8 \text{ k}\text{\AA}$

Backside metallization: None

Glassivation.

Type: Nitride

Thickness: $4.0 \text{ k}\text{\AA} \pm 0.5 \text{ k}\text{\AA}$

Substrate: Dielectrically isolated (DI), Bipolar

Assembly related information.

Substrate potential: Unbiased

Special assembly instructions: None

FIGURE A-1. Die bonding pad locations and electrical functions - continued.

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STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 20-04-17

Approved sources of supply for SMD 5962-07218 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DLA Land and Maritime-VA. This information bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535. DLA Land and Maritime maintains an online database of all current sources of supply at <https://landandmaritimeapps.dla.mil/programs/smcr/>.

Standard microcircuit drawing PIN <u>1/</u>	Vendor CAGE number	Vendor similar PIN <u>2/</u>
5962F0721801VEA	<u>3/</u>	ISL73096RHVD
5962F0721801VXC	34371	ISL73096RHVF
5962F0721801V9A	34371	ISL73096RHVX
5962F0721802VEA	<u>3/</u>	ISL73127RHVD
5962F0721802VXC	34371	ISL73127RHVF
5962F0721802V9A	34371	ISL73127RHVX
5962F0721803VEA	<u>3/</u>	ISL73128RHVD
5962F0721803VXC	34371	ISL73128RHVF
5962F0721803V9A	34371	ISL73128RHVX
5962F0721804VXC	34371	ISL73096EHVF
5962F0721804V9A	34371	ISL73096EHVX
5962F0721805VXC	34371	ISL73127EHVF
5962F0721805V9A	34371	ISL73127EHVX
5962F0721806VXC	34371	ISL73128EHVF
5962F0721806V9A	34371	ISL73128EHVX

- 1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.
- 2/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.
- 3/ Not available from an approved source of supply.

Vendor CAGE
number

34371

Vendor name
and address

Renesas Electronics America, Inc.
1650 Robert J. Conlan Blvd. NE
Palm Bay, FL 32905-3406

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.